



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

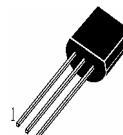
H926

POWER SUPPLIES, RELAY DRIVERS,
LAMP DRIVERS, ELECTRICAL EQUIPMENT

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

T_{stg}	Storage Temperature	-55~150 $^{\circ}\text{C}$
T_j	Junction Temperature	150 $^{\circ}\text{C}$
P_C	Collector Dissipation	750mW
V_{CBO}	Collector-Base Voltage	-30V
V_{CEO}	Collector-Emitter Voltage	-25V
V_{EBO}	Emitter-Base Voltage	-6V
I_C	Collector Current	-2A

TO-92



1—Emitter, E
2—Collector, C
3—Base, B

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-30			V	$I_C=-10\mu\text{A}$, $I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-25			V	$I_C=-1\text{mA}$, $I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	-6			V	$I_E=-10\mu\text{A}$, $I_C=0$
$H_{\text{FE}}(1)$	DC Current Gain	100		560		$V_{\text{CE}}=-2\text{V}$, $I_C=-100\text{mA}$
$H_{\text{FE}}(2)$		65	130			$V_{\text{CE}}=-2\text{V}$, $I_C=-1.5\text{A}$ *
$V_{\text{CE}}(\text{sat})$	Collector- Emitter Saturation Voltage		-0.35	-0.6	V	$I_C=-1.5\text{A}$, $I_B=-75\text{mA}$ *
$V_{\text{BE}}(\text{sat})$	Base-Emitter Saturation Voltage		-0.85	-1.2	V	$I_C=-1.5\text{A}$, $I_B=-75\text{mA}$ *
I_{CBO}	Collector Cut-off Current			-100	nA	$V_{\text{CB}}=-20\text{V}$, $I_E=0$
I_{EBO}	Emitter Cut-off Current			-100	nA	$V_{\text{EB}}=-4\text{V}$, $I_C=0$
f_T	Current Gain-Bandwidth Product		150		MHz	$V_{\text{CE}}=-10\text{V}$, $I_C=-50\text{mA}$
C_{ob}	Output Capacitance		32		pF	$V_{\text{CB}}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$

* pulse

h_{FE} Classification

R

S

T

U

100—200

140—280

200—400

280—560

